


This Page Is Inserted by IFW Operations
and is not a part of the Official Record

BEST AVAILABLE IMAGES

Defective images within this document are accurate representations of the original documents submitted by the applicant.

Defects in the images may include (but are not limited to):

- BLACK BORDERS
-  TEXT CUT OFF AT TOP, BOTTOM OR SIDES
- FADED TEXT
- ILLEGIBLE TEXT
- SKEWED/SLANTED IMAGES
- COLORED PHOTOS
- BLACK OR VERY BLACK AND WHITE DARK PHOTOS
- GRAY SCALE DOCUMENTS

IMAGES ARE BEST AVAILABLE COPY.

**As rescanning documents *will not* correct images,
please do not report the images to the
Image Problem Mailbox.**

INFORMATION DISCLOSURE CITATION
(Use several sheets if necessary)

Docket Number (Optional)
SETI-0001

Application Number
09/966563

Applicant(s)
Khan et al.

Filing Date
September 27, 2001

Group Art Unit
2814

U.S. PATENT DOCUMENTS

| *EXAMINER INITIAL | REF | DOCUMENT NUMBER | DATE | NAME | CLASS | SUBCLASS | FILING DATE IF APPROPRIATE |
|----------------------|-----|-----------------|------|------|-------|----------|-------------------------------|
| | | | | | | | |
| | | | | | | | |
| | | | | | | | |
| | | | | | | | |
| | | | | | | | |
| | | | | | | | |
| | | | | | | | |
| | | | | | | | |
| | | | | | | | |
| | | | | | | | |
| | | | | | | | |
| | | | | | | | |
| | | | | | | | |
| | | | | | | | |
| | | | | | | | |
| | | | | | | | |
| | | | | | | | |
| | | | | | | | |
| | | | | | | | |
| | | | | | | | |
| | | | | | | | |

FOREIGN PATENT DOCUMENTS

| | REF | DOCUMENT NUMBER | DATE | COUNTRY | CLASS | SUBCLASS | Translation | |
|--|-----|-----------------|------|---------|-------|----------|-------------|----|
| | | | | | | | YES | NO |
| | | | | | | | | |
| | | | | | | | | |
| | | | | | | | | |
| | | | | | | | | |
| | | | | | | | | |
| | | | | | | | | |
| | | | | | | | | |
| | | | | | | | | |

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

| | | |
|--|--|--|
| | | "The Influence of the Strain-Induced Electric Field on the Charge Distribution in GaN-AlN-GaN Structure," A. D. Bykhovski et al., Journal of Applied Physics, Vol. 74, No. 11, December 1, 1993, pp.6734-6739. |
| | | "Pyroelectricity in Gallium Nitride Thin Films," A. D. Bykhovski et al., Applied Physics Letters, Vol. 69, No. 21, November 18, 1996, pp. 3254-3256. |

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

| | | | |
|---|--|--|--|
| INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i> | | Docket Number (Optional) SETI-0001 | Application Number 09/966563 |
| | | Applicant(s) Khan et al. | |
| | | Filing Date September 27, 2001 | Group Art Unit 2814 |
| *EXAMINER INITIAL | OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i> | | |
| | "Pyroelectric and Piezoelectric Properties of GaN-Based Materials," M. S. Shur et al., MRS Internet J. Nitride Semicond. Res. 4S1, G1.6 (1999), pp. 1-12. | | |
| | "Piezoeffect and Gate Current in AlGaIn/GaN High Electron Mobility Transistors," R. Gaska et al., Applied Physics Letters, Vol. 71, No. 25, December 22, 1997, pp. 3673-3675. | | |
| | "Two-Dimensional Electron-Gas Density in Al _x Ga _{1-x} N/GaN Heterostructure Field-Effect Transistors," N. Maeda et al., Applied Physics Letters, Vol. 73, No. 13, September 28, 1998, pp. 1856-1858. | | |
| | "Piezoelectric Charge Densities in AlGaIn/GaN HFETs," P.M. Asbeck et al., Electronic Letters, Vol. 33, No. 14, July 3, 1997, 1230-1231. | | |
| | "Spontaneous Polarization and Piezoelectric Constants of III-V Nitrides," F. Bernardini et al., Physical Review B, Vol. 56, No. 16, October 15, 1997, pp. R10024-R10027. | | |
| | "Piezoelectric Doping and Elastic Strain Relaxation in AlGaIn-GaN Heterostructure Field Effect Transistors," A. D. Bykhovski et al., Applied Physics Letters, Vol. 73, No. 24, December 14, 1998, pp. 3577-3579. | | |
| | "Ferroelectric Semiconductors," V. M. Fridkin, Russia (1976), p. 90 (pp. 64-65 in English version). | | |
| | "Lattice and Energy Band Engineering in AlInGaIn/GaN Heterostructures," M. A. Khan et al., Applied Physics Letters, Vol. 76, No. 9, February 28, 2000, pp. 1161-1163. | | |
| | "Electron Mobility in Modulation-Doped AlGaIn-GaN Heterostructures," R. Gaska et al., Applied Physics Letters, Vol. 74, No. 2, January 11, 1999, pp. 287-289. | | |
| | "High Pinch-off Voltage AlGaIn-GaN Heterostructure Field Effect Transistor," M. S. Shur et al., Proceedings of ISDRS-97, Charlottesville, VA, December 1997, pp. 377-380. | | |
| | "Optoelectronic GaN-Based Field Effect Transistors," M. S. Shur et al., SPIE Vol. 2397, pp. 294-303. | | |
| | "Current/Voltage Characteristic Collapse in AlGaIn/GaN Heterostructure Insulated Gate Field Effect Transistors at High Drain Bias," M. A. Khan et al., Electronic Letters, Vol. 30, No. 25, December 8, 1994, pp. 2175-2176. | | |
| EXAMINER | | DATE CONSIDERED | |
| <p>*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</p> | | | |

| | | | |
|-----------------------------------|---------------------------------------|---|-------------|
| Notice of References Cited | Application/Control No. 09/966,563 | Applicant(s)/Patent Under Reexamination KHAN ET AL. | |
| | Examiner Long Pham | Art Unit 2814 | Page 1 of 1 |

U.S. PATENT DOCUMENTS

| * | | Document Number Country Code-Number-Kind Code | Date MM-YYYY | Name | Classification |
|---|---|--|-----------------|-----------------|----------------|
| | A | US-US006359292B1 | 03-2002 | Sugawara et al. | |
| | B | US-US005851905A | 12-1998 | McIntosh et al. | |
| | C | US-US006316793B1 | 11-2001 | Sheppard et al. | |
| | D | US-US005981977A | 11-1999 | Furukawa et al. | |
| | E | US- | | | |
| | F | US- | | | |
| | G | US- | | | |
| | H | US- | | | |
| | I | US- | | | |
| | J | US- | | | |
| | K | US- | | | |
| | L | US- | | | |
| | M | US- | | | |

FOREIGN PATENT DOCUMENTS

| * | | Document Number Country Code-Number-Kind Code | Date MM-YYYY | Country | Name | Classification |
|---|---|--|-----------------|---------|------|----------------|
| | N | | | | | |
| | O | | | | | |
| | P | | | | | |
| | Q | | | | | |
| | R | | | | | |
| | S | | | | | |
| | T | | | | | |

NON-PATENT DOCUMENTS

| * | | Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages) |
|---|---|---|
| | U | |
| | V | |
| | W | |
| | X | |

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.